

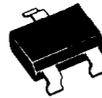
# SST201 SERIES N-Channel JFETs

The SST201 Series is the SOT-23 equivalent of our popular J201 Series. It features low leakage, very low noise, and low cutoff voltage for use with low level power supplies. The SST201 is excellent for battery operated equipment and low current amplifiers. The SST201 Series SOT-23 package affords low cost and compatibility with automated assembly techniques. (See Section 7.)

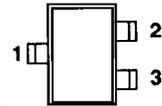
PART NUMBER	$V_{GS(OFF)}$ MAX (V)	$V_{(BR)GSS}$ MIN (V)	$\theta_{fs}$ MIN (mS)	$I_{DSS}$ MAX (mA)
SST201	-1.5	-40	0.5	1
SST202	-4	-40	1	4.5

For further design information please consult the typical performance curves NPA.

SOT-23



TOP VIEW



1 GATE  
2 SOURCE  
3 DRAIN

## SIMILAR PRODUCTS

- TO-92, See J201 Series
- TO-18, See 2N4338 Series
- Chips, See NPA Series Die

### PRODUCT MARKING

SST201	P01
SST202	P02

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Gate-Drain Voltage	$V_{GD}$	-40	V
Gate-Source Voltage	$V_{GS}$	-40	
Gate Current	$I_G$	50	mA
Power Dissipation	$P_D$	350	mW
Power Derating		2.8	mW/ $^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	
Lead Temperature ( $1/16"$ from case for 10 sec.)	$T_L$	300	

# SST201 SERIES



SPECIFICATIONS <sup>a</sup>				LIMITS				
PARAMETER	SYMBOL	TEST CONDITIONS	TYP <sup>b</sup>	SST201		SST202		UNIT
				MIN	MAX	MIN	MAX	
<b>STATIC</b>								
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = -1 \mu A, V_{DS} = 0 V$	-57	-40		-40		V
Gate-Source Cutoff Voltage	$V_{GS(OFF)}$	$V_{DS} = 20 V, I_D = 10 nA$		-0.3	-1.5	-0.8	-4	
Saturation Drain Current <sup>c</sup>	$I_{DSS}$	$V_{DS} = 20 V, V_{GS} = 0 V$		0.2	1	0.9	4.5	mA
Gate Reverse Current	$I_{GSS}$	$V_{GS} = -20 V, V_{DS} = 0 V$	-2		-100		-100	pA
		$T_A = 125^\circ C$	-1					nA
Gate Operating Current	$I_G$	$V_{DG} = 15 V, I_D = 0.1 mA$	-2					pA
Drain Cutoff Current	$I_{D(OFF)}$	$V_{DS} = 15 V, V_{GS} = -10 V$	2					
Gate-Source Forward Voltage	$V_{GS(F)}$	$I_G = 1 mA, V_{DS} = 0 V$	0.7					V
<b>DYNAMIC</b>								
Common-Source Forward Transconductance	$g_{fs}$	$V_{DG} = 20 V, V_{GS} = 0 V$ $f = 1 kHz$		0.5		1		mS
Common-Source Input Capacitance	$C_{iss}$	$V_{DS} = 20 V, V_{GS} = 0 V$ $f = 1 MHz$	4.5					pF
Common-Source Reverse Transfer Capacitance	$C_{rss}$		1.3					
Equivalent Input Noise Voltage	$\bar{e}_n$	$V_{DS} = 10 V, V_{GS} = 0 V$ $f = 1 kHz$	6					$\frac{nV}{\sqrt{Hz}}$

**NOTES:**

- a.  $T_A = 25^\circ C$  unless otherwise noted.
- b. For design aid only, not subject to production testing.
- c. Pulse test;  $PW = 300 \mu S$ , duty cycle  $\leq 3\%$ .